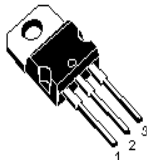
STP6NK90Z - STP6NK90ZFP
STB6NK90Z - STW7NK90Z

N-channel 900V - 1.56Ω - 5.8A - TO-220/TO-220FP/D²PAK/TO-247
Zener-protected SuperMESH™ Power MOSFET

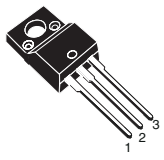
Features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STP6NK90Z	900 V	< 2 Ω	5.8 A
STP6NK90ZFP	900 V	< 2 Ω	5.8 A
STB6NK90Z	900 V	< 2 Ω	5.8 A
STW7NK90Z	900 V	< 2 Ω	5.8 A

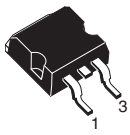
- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



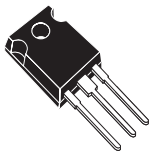
TO-220



TO-220FP



D²PAK



TO-247

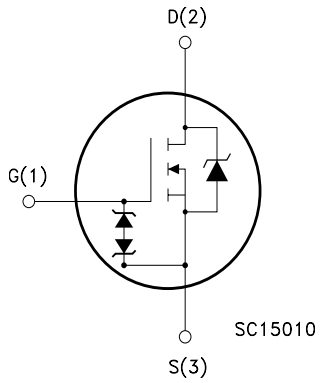
Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs.

Application

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP6NK90Z	P6NK90Z	TO-220	Tube
STP6NK90ZFP	P6NK90ZFP	TO-220FP	Tube
STB6NK90ZT4	B6NK90Z	D²PAK	Tape e reel
STW7NK90Z	W7NK90Z	TO-247	Tube

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/ D^2PAK/TO247	TO220FP	
V_{DS}	Drain-source voltage (V_{GS} = 0)	900		V
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at T_C = 25°C	5.8	5.8 (1)	A
I_D	Drain current (continuous) at T_C = 100°C	3.65	3.65 (1)	A
I_{DM} (2)	Drain current (pulsed)	23.2	23.2 (1)	A
P_{TOT}	Total dissipation at T_C = 25°C	140	30	W
	Derating factor	1.12	0.24	W/°C
dv/dt (3)	Peak diode recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; Tc= 25°C)	-	2500	V
T_j T_{stg}	Max operating junction temperature Storage temperature	-55 to 150		°C °C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤5.8 A, di/dt ≤200A/µs, V_{DD} ≤$V_{(BR)DSS}$, T_j ≤$T_{JMAX.}$

Table 2. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	D^2PAK	TO-220FP	TO-247	
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.89		4.2	0.89	°C/W
$R_{thj\text{-}pcb}$	Thermal resistance junction-case max		60			°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	62.5			50	°C/W
T_l	Maximum lead temperature for soldering purpose	300				°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	5.8	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=50V)	300	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	Igs=± 1mA (Open Drain)	30			V

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	I_D =1mA, V_{GS} = 0	900			V
I_{DSS}	Zero gate voltage Drain current (V_{GS} = 0) V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125°C				1 50	µA µA
I_{GSS}	Gate-body leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 2.9 A		1.56	2	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15v, I_D = 2.9 A		5		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0		1350 130 26		pF pF pF
$C_{oss\ eq.}$ (2)	Equivalent output capacitance	V_{DS} =0V, V_{DS} = 0V to 720V		70		pF
$t_{d(on)}$ t_r $t_{r(off)}$ t_r	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 450 V, I_D = 3 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 20*)		17 45 20 20		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 720 V, I_D = 5.8 A, V_{GS} = 10 V		46.5 8.5 25	60.5	nC nC nC
$T_{r(Voff)}$ T_r T_c	Off-voltage rise time Fall time Cross-over time	V_{DD} = 720 V, I_D = 5.8 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 22*)		11 12 20		ns ns ns

1. Pulsed: pulse duration=300µs, duty cycle 1.5%
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(1)	Source-drain current Source-drain current (pulsed)				5.8 23.2	A A
V_{SD}(2)	Forward on voltage	I_{SD} = 5.8 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 5.8 A, di/dt = 100 A/µs V_{DD} = 36 V, Tj = 150°C (see *Figure 22*)		840 5880 14		ns µC A

1. Pulsed: pulse duration=300µs, duty cycle 1.5%
2. Pulse width limited by safe operating area

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/ D²PAK

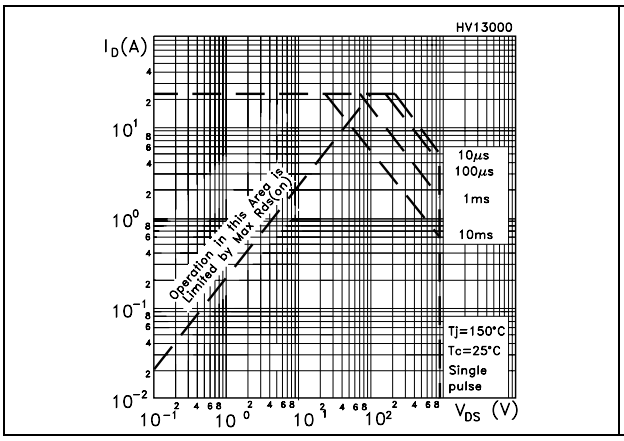


Figure 2. Thermal impedance for TO-220/ D²PAK

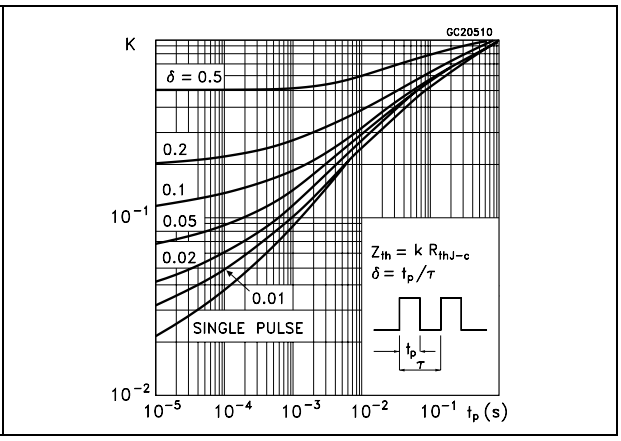


Figure 3. Safe operating area for TO-220FP

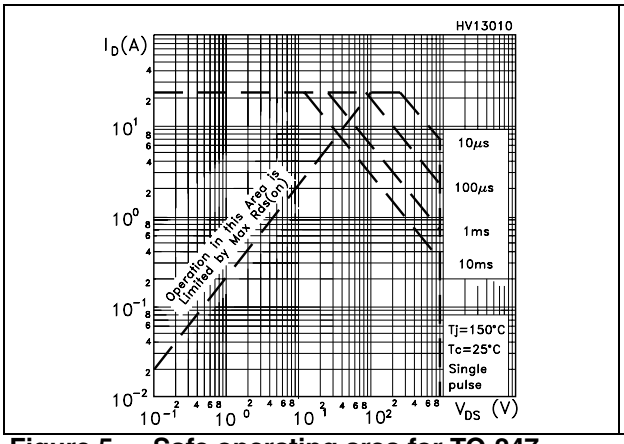


Figure 4. Thermal impedance for TO-220FP

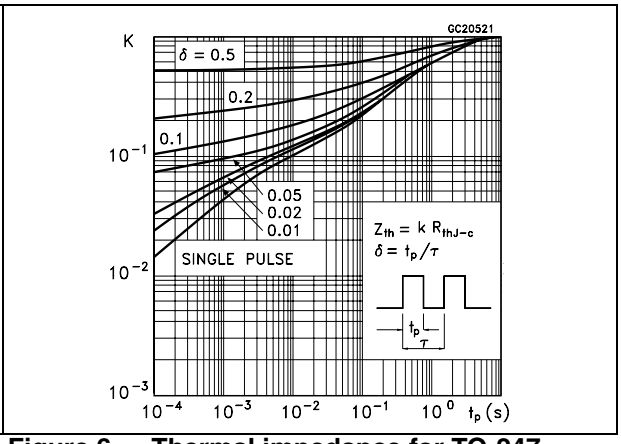


Figure 5. Safe operating area for TO-247

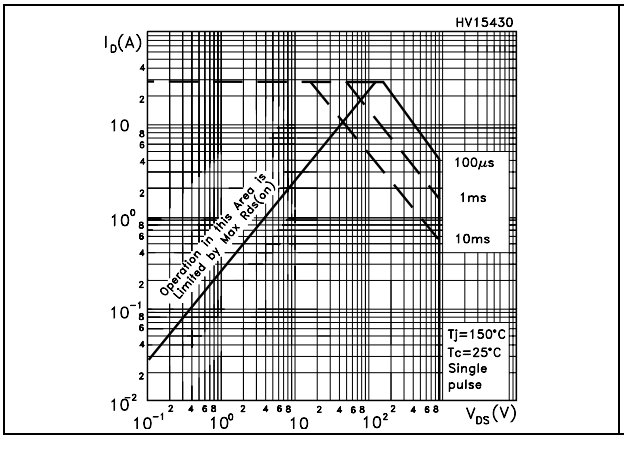


Figure 6. Thermal impedance for TO-247

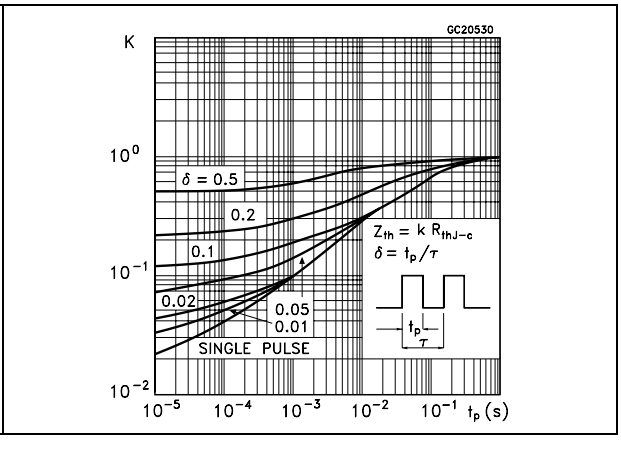


Figure 7. Output characterisics

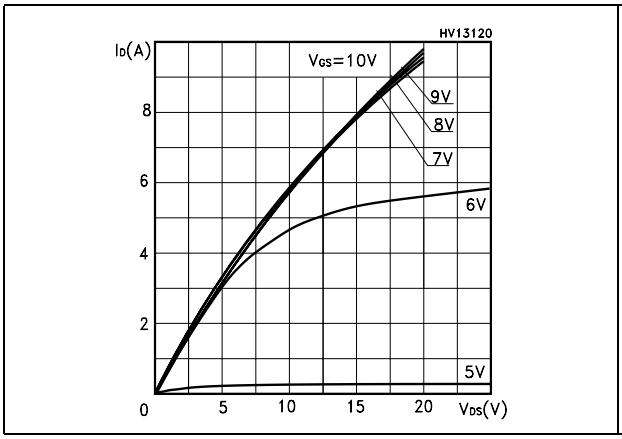


Figure 8. Transfer characteristics

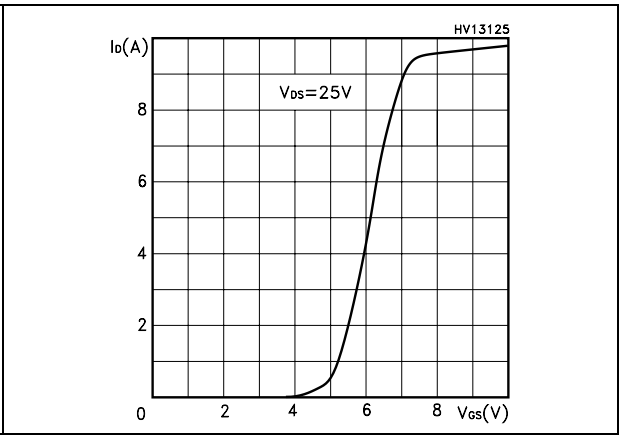


Figure 9. Transconductance

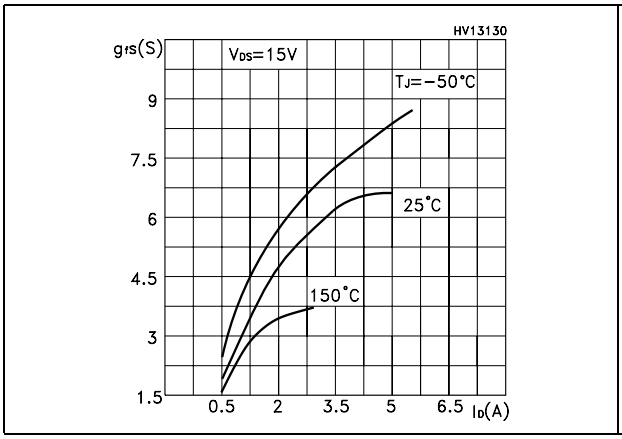


Figure 10. Static drain-source on resistance

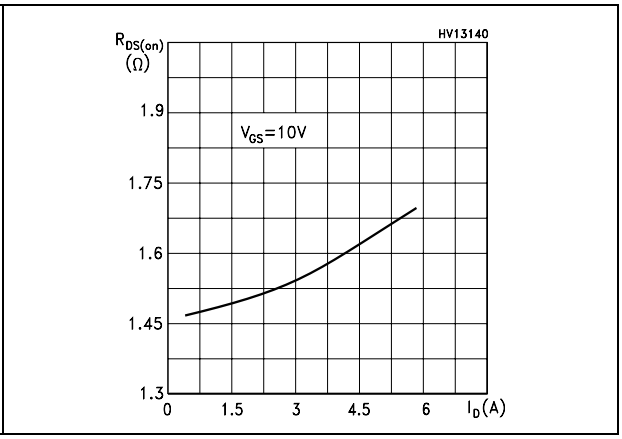


Figure 11. Gate charge vs gate-source voltage

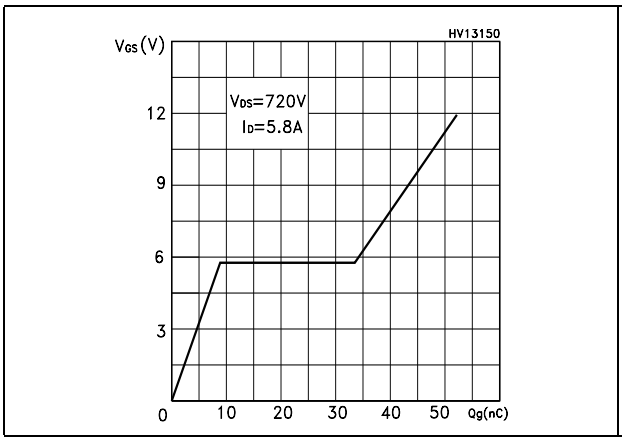


Figure 12. Capacitance variations

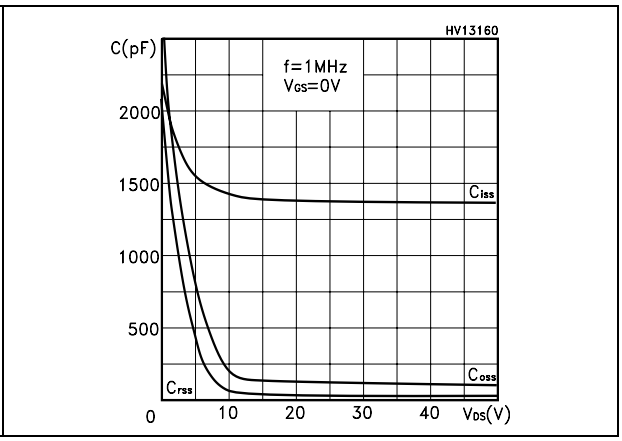


Figure 13. Normalized gate threshold voltage vs temperature

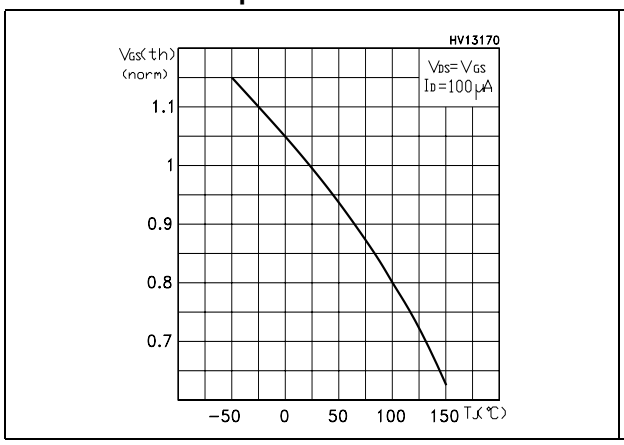


Figure 14. Normalized on resistance vs temperature

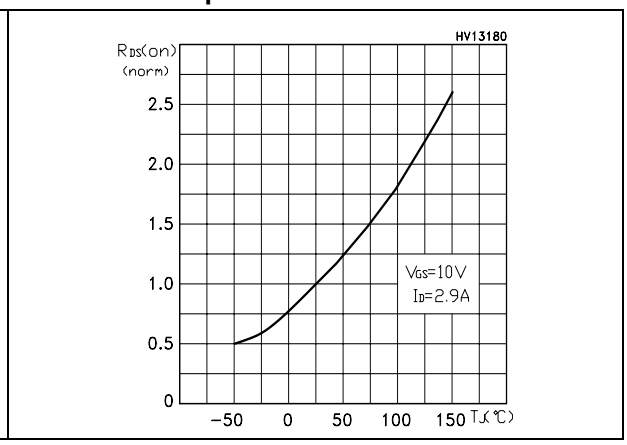


Figure 15. Source-drain diode forward characteristic

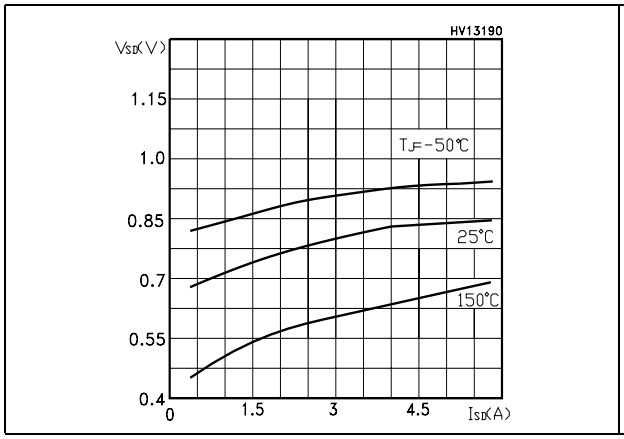


Figure 16. Normalized BVDSS vs temperature

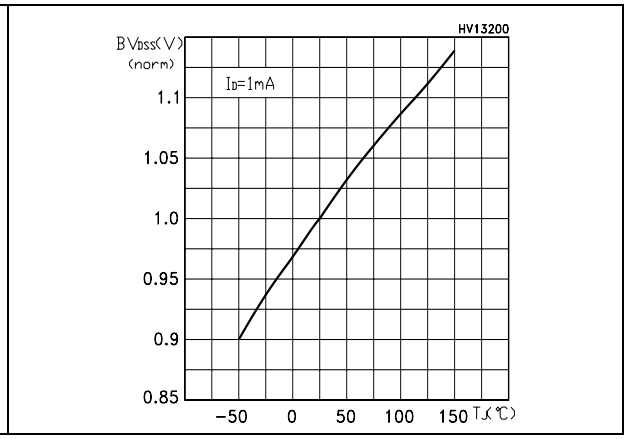
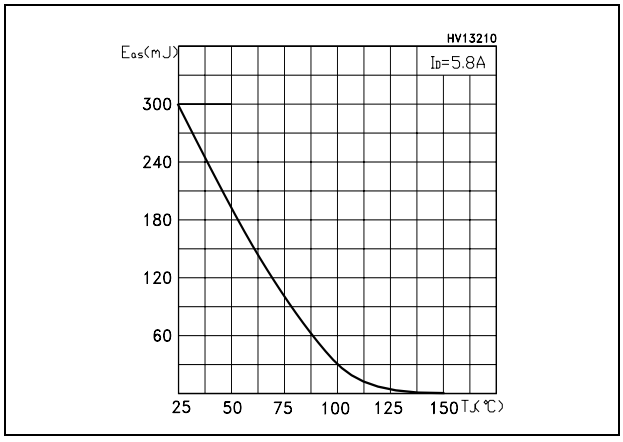


Figure 17. Maximum avalanche energy vs temperature



3 Test circuit

Figure 18. Unclamped inductive load test circuit

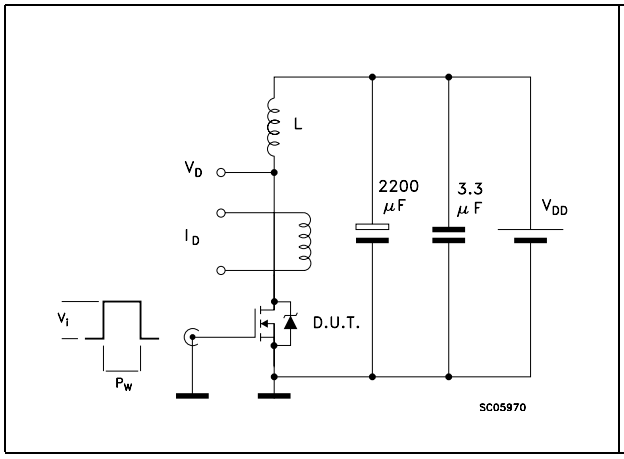


Figure 19. Unclamped inductive waveform

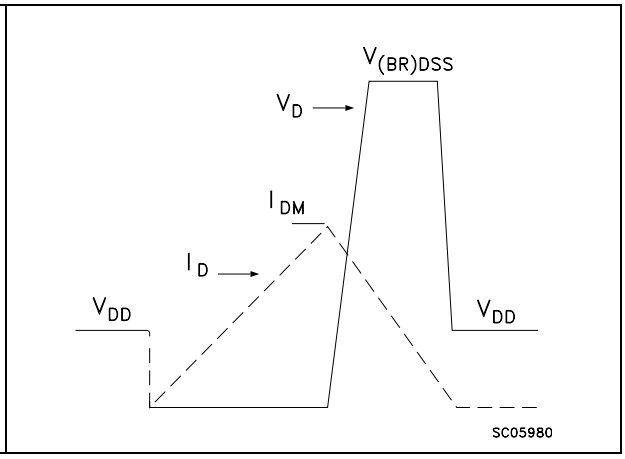


Figure 20. Switching times test circuit for resistive load

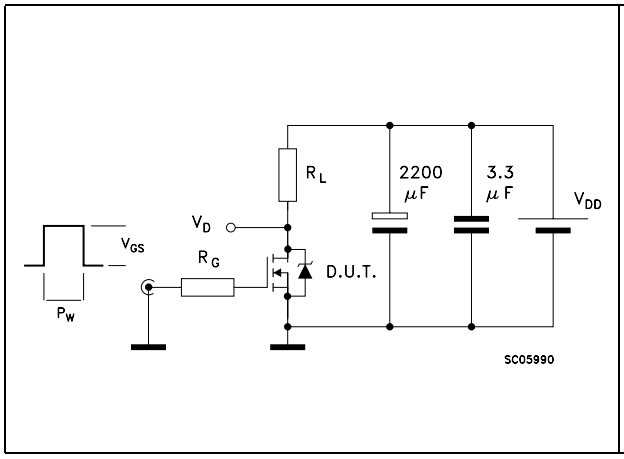


Figure 21. Gate charge test circuit

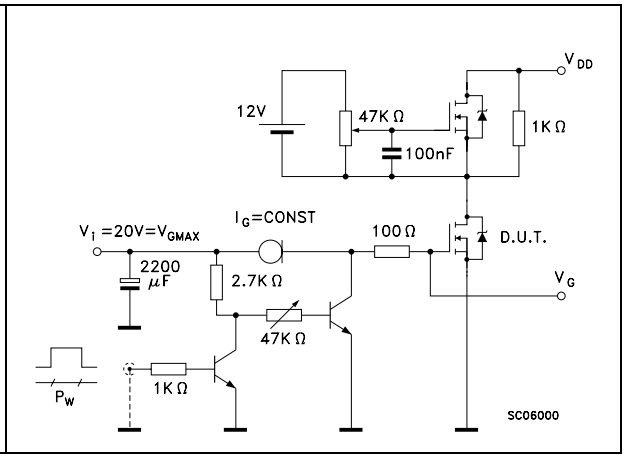
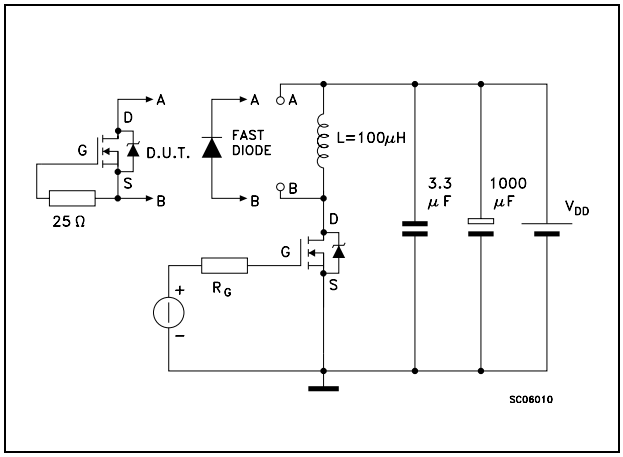


Figure 22. Test circuit for inductive load switching and diode recovery times

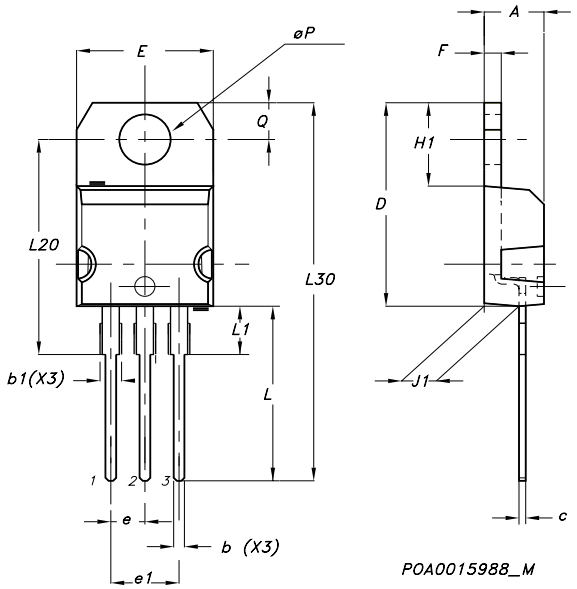


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

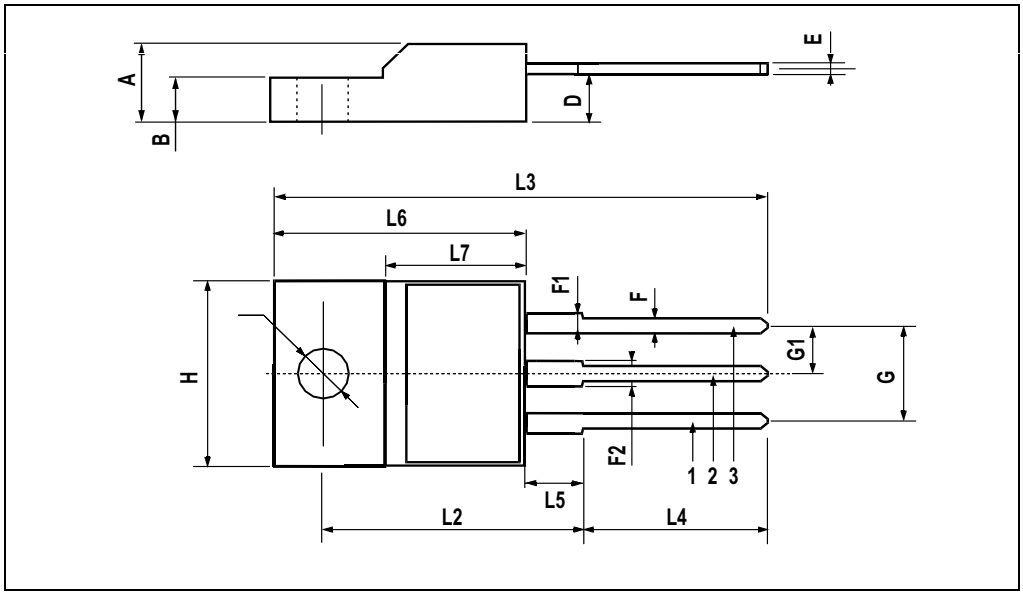
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



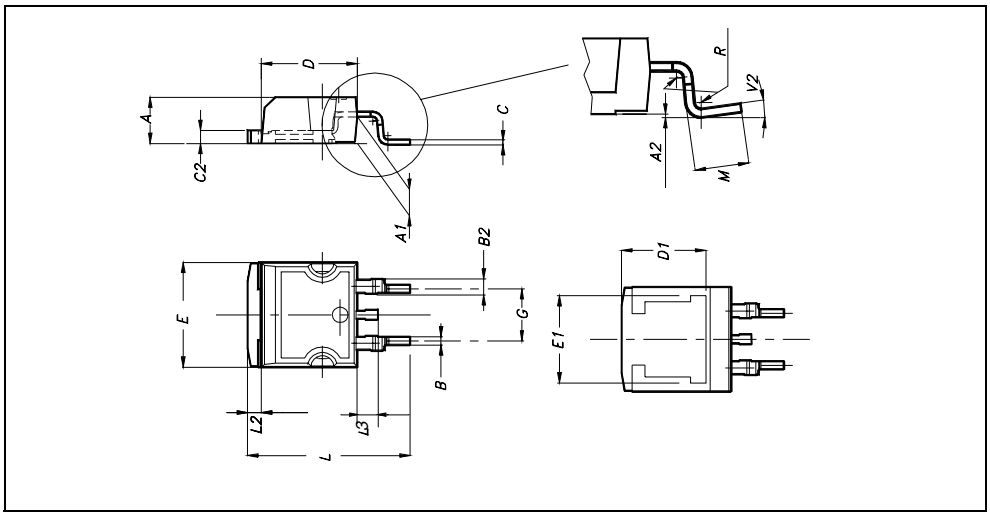
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



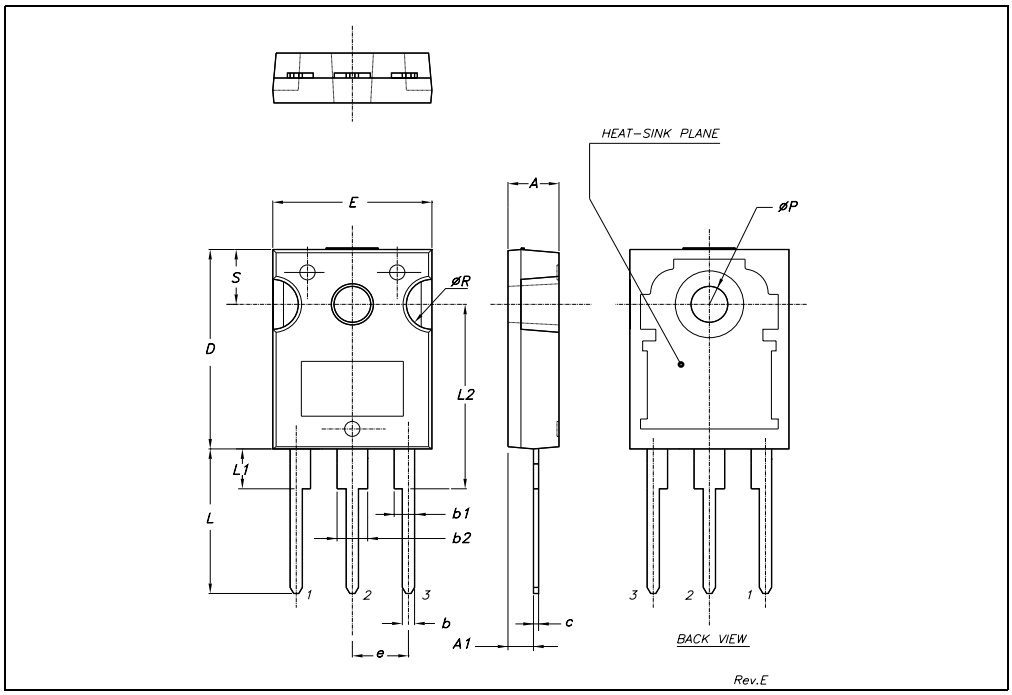
D^2PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



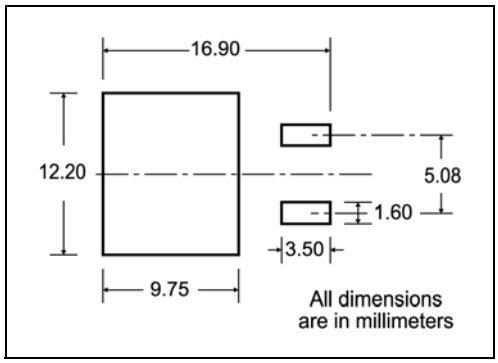
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

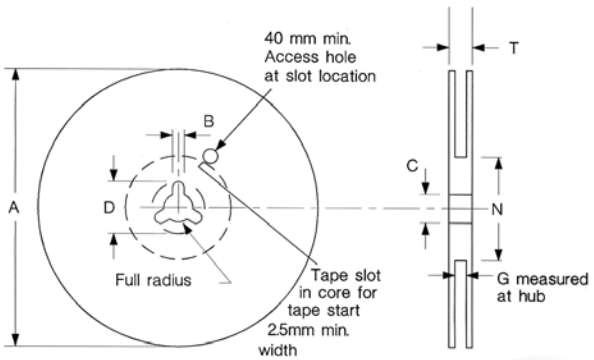


5 Packaging mechanical data

D^2PAK FOOTPRINT



TAPE AND REEL SHIPMENT



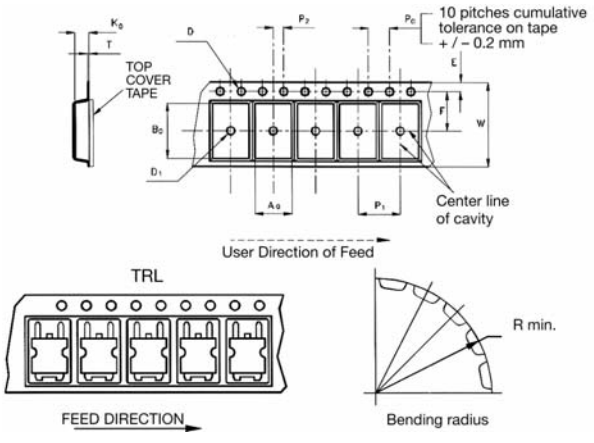
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
29-Nov-2005	3	Complete version
16-Aug-2006	4	New template, no content change
10-Apr-2007	5	Typo mistake on *Table 2*

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